



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of:

Chihiro Uchibori

Group Art Unit: .2825

Application No.: 09/648,750

Examiner: Granville Lee

Filed: August 28, 2000

Docket No.: 108077-00000

For: METAL INTERCONNECTION, SEMICONDUCTOR DEVICE, METHOD FOR FORMING METAL INTERCONNECTION AND METHOD FOR FABRICATING SEMICONDUCTOR DEVICE

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**AMENDMENT UNDER 37 C.F.R. § 1.121**

Commissioner for Patents  
Washington, D.C. 20231

March 21, 2002

Sir:

In reply to the Office Action mailed December 21, 2001, please amend the above-identified application as follows:

**IN THE CLAIMS:**

Please amend the claims as follows. A marked-up version of the claims is attached hereto.

1. (Amended) A metal interconnection buried in an insulation film comprising: an interconnection material containing copper as a main component; a barrier layer formed between the insulation film and the interconnection material; and an adhesion layer containing zirconium formed between the barrier layer and the interconnection material, the adhesion layer being for improving an adhesion between the barrier layer and the interconnection material.
2. (Amended) A metal interconnection buried in an insulation film comprising: an interconnection material containing copper as a main component;